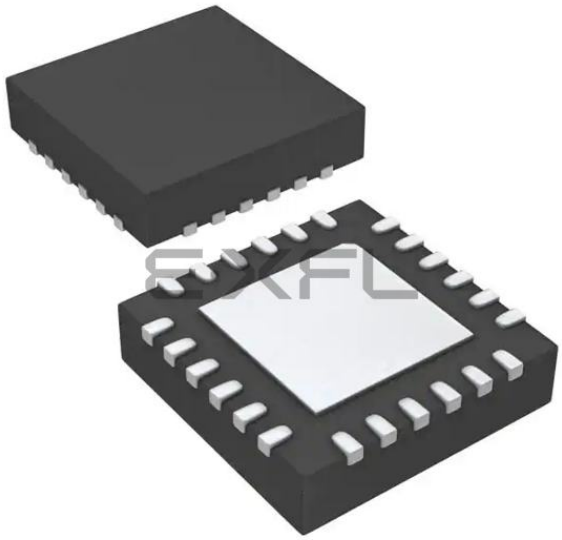

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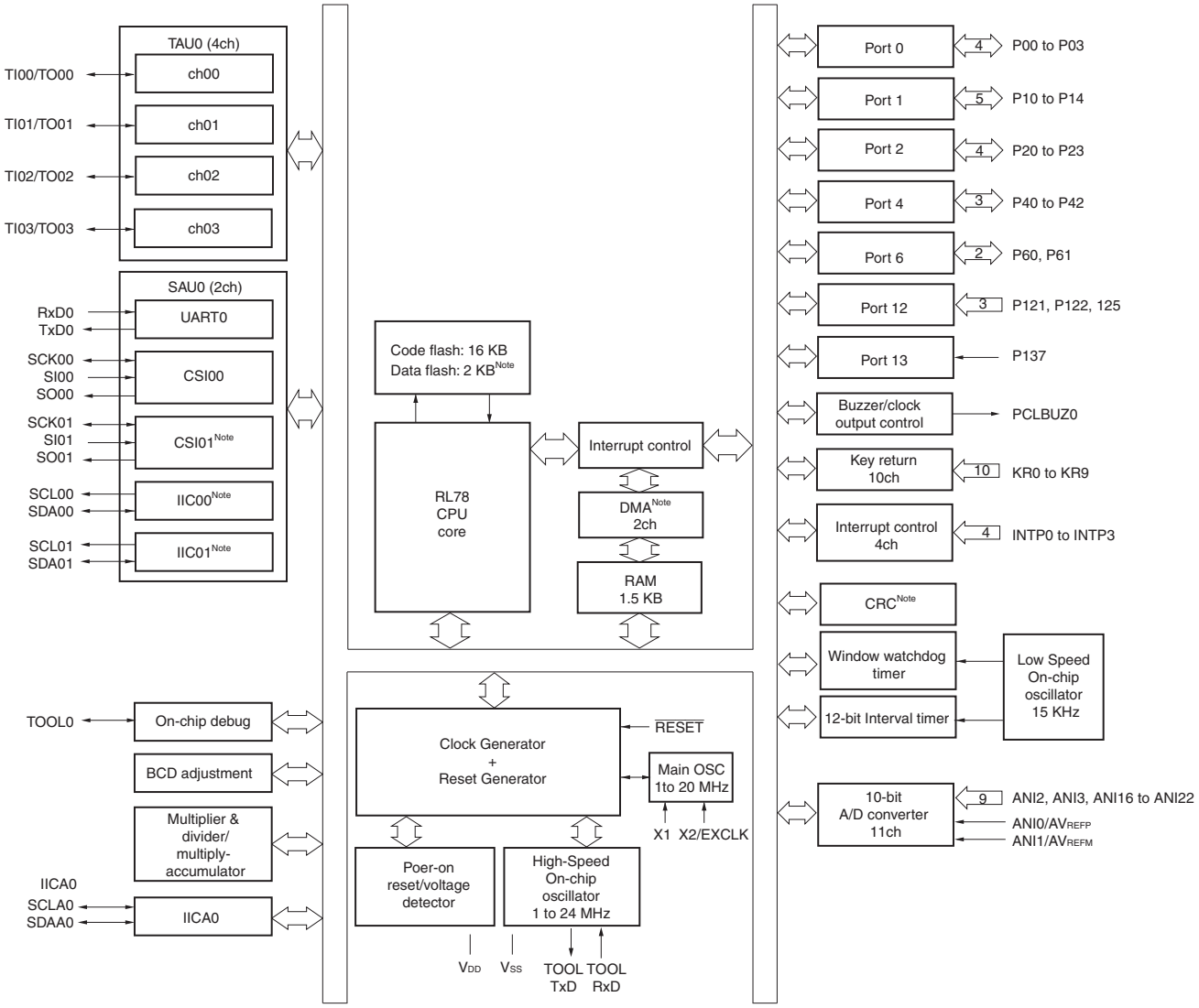
Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I²C, UART/USART
Peripherals	LVD, POR, PWM, WDT
Number of I/O	18
Program Memory Size	4KB (4K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	512 x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 11x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	24-WFQFN Exposed Pad
Supplier Device Package	24-HWQFN (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f10377dna-u0

1.6.2 24-pin products



Note Provided only in the R5F102 products.

(2) 30-pin products

(T_A = –40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(1/2)**

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD1}	Operating mode	HS (High-speed main) mode Note 4	f_{IH} = 24 MHz Note 3	Basic operation	V_{DD} = 5.0 V		1.5		mA
						V_{DD} = 3.0 V		1.5		
					Normal operation	V_{DD} = 5.0 V		3.7	5.5	mA
						V_{DD} = 3.0 V		3.7	5.5	
				f_{IH} = 16 MHz Note 3		V_{DD} = 5.0 V		2.7	4.0	mA
						V_{DD} = 3.0 V		2.7	4.0	
			LS (Low-speed main) mode Note 4	f_{IH} = 8 MHz Note 3		V_{DD} = 3.0 V		1.2	1.8	mA
						V_{DD} = 2.0 V		1.2	1.8	
			HS (High-speed main) mode Note 4	f_{MX} = 20 MHz Note 2, V_{DD} = 5.0 V		Square wave input		3.0	4.6	mA
						Resonator connection		3.2	4.8	
				f_{MX} = 20 MHz Note 2, V_{DD} = 3.0 V		Square wave input		3.0	4.6	mA
						Resonator connection		3.2	4.8	
				f_{MX} = 10 MHz Note 2, V_{DD} = 5.0 V		Square wave input		1.9	2.7	mA
						Resonator connection		1.9	2.7	
				f_{MX} = 10 MHz Note 2, V_{DD} = 3.0 V		Square wave input		1.9	2.7	mA
						Resonator connection		1.9	2.7	
			LS (Low-speed main) mode Note 4	f_{MX} = 8 MHz Note 2, V_{DD} = 3.0 V		Square wave input		1.1	1.7	mA
						Resonator connection		1.1	1.7	
				f_{MX} = 8 MHz Note 2, V_{DD} = 2.0 V		Square wave input		1.1	1.7	mA
						Resonator connection		1.1	1.7	

Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. When high-speed on-chip oscillator clock is stopped.

3. When high-speed system clock is stopped

4. Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS(High speed main) mode: V_{DD} = 2.7 V to 5.5 V @1 MHz to 24 MHz
V_{DD} = 2.4 V to 5.5 V @1 MHz to 16 MHz

LS(Low speed main) mode: V_{DD} = 1.8 V to 5.5 V @1 MHz to 8 MHz

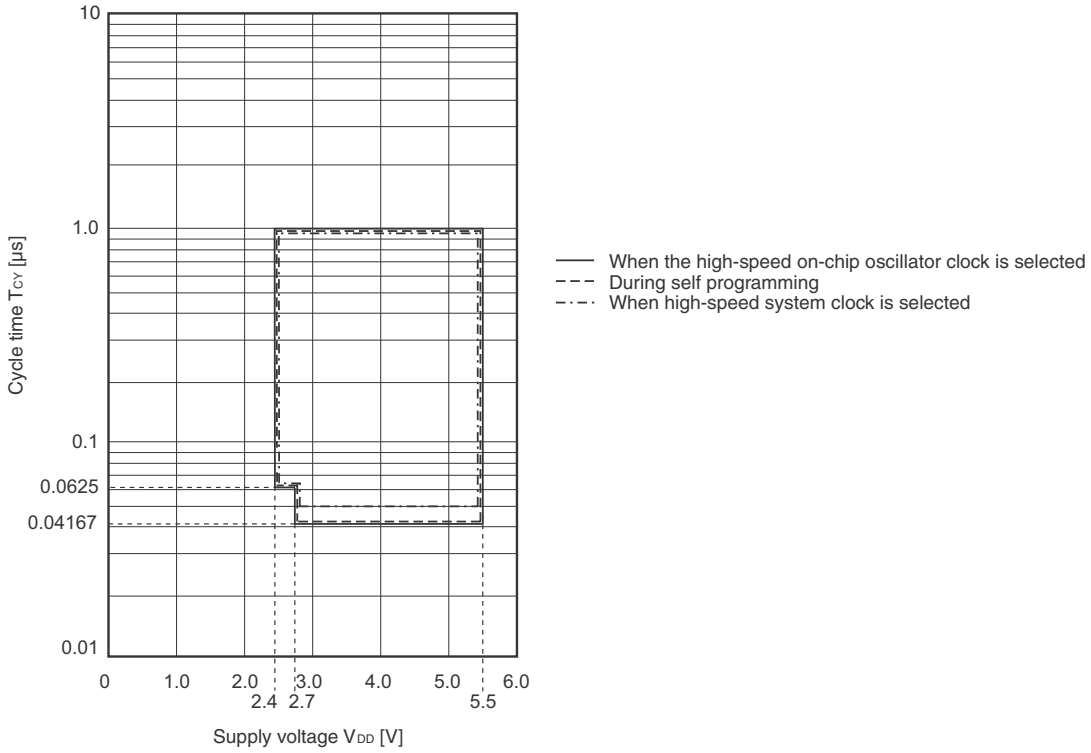
Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

2. f_{IH}: high-speed on-chip oscillator clock frequency

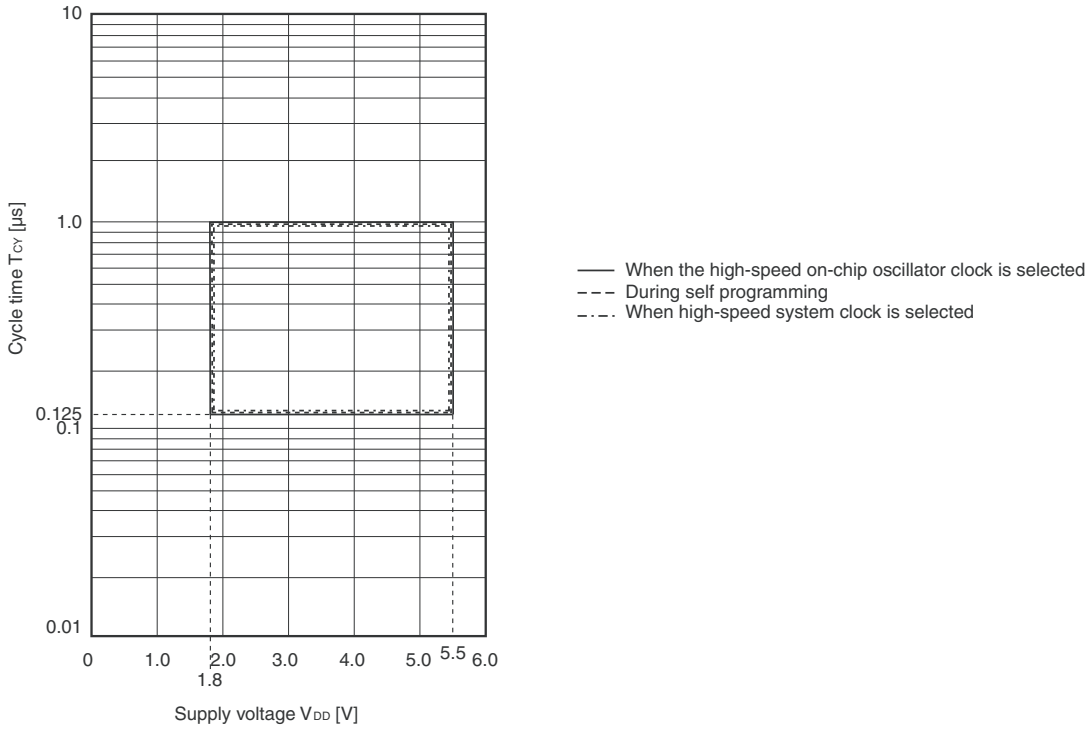
3. Temperature condition of the TYP. value is T_A = 25°C.

Minimum Instruction Execution Time during Main System Clock Operation

T_{CY} vs V_{DD} (HS (high-speed main) mode)



T_{CY} vs V_{DD} (LS (low-speed main) mode)



(3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output)

(T_A = −40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq 4/f_{CLK}$	2.7 V ≤ V_{DD} ≤ 5.5 V	167		500		ns
			2.4 V ≤ V_{DD} ≤ 5.5 V	250		500		ns
			1.8 V ≤ V_{DD} ≤ 5.5 V	–		500		ns
SCKp high-/low-level width	t_{KH1}, t_{KL1}	4.0 V ≤ V_{DD} ≤ 5.5 V		t_{KCY1}/2−12		t_{KCY1}/2−50		ns
		2.7 V ≤ V_{DD} ≤ 5.5 V		t_{KCY1}/2−18		t_{KCY1}/2−50		ns
		2.4 V ≤ V_{DD} ≤ 5.5 V		t_{KCY1}/2−38		t_{KCY1}/2−50		ns
		1.8 V ≤ V_{DD} ≤ 5.5 V		–		t_{KCY1}/2−50		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	4.0 V ≤ V_{DD} ≤ 5.5 V		44		110		ns
		2.7 V ≤ V_{DD} ≤ 5.5 V		44		110		ns
		2.4 V ≤ V_{DD} ≤ 5.5 V		75		110		ns
		1.8 V ≤ V_{DD} ≤ 5.5 V		–		110		ns
SIp hold time (from SCKp↑) Note 2	t_{KSI1}			19		19		ns
Delay time from SCKp↓ to SOp output Note 3	t_{KSO1}	C = 30 pF Note4			25		25	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp and SCKp pins by using port input mode register 1 (PIM1) and port output mode registers 0, 1, 4 (POM0, POM1, POM4).

Remarks 1. p: CSI number (p = 00, 01, 11, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3: "1, 3" is only for the R5F102 products)

2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3: "1, 3" is only for the R5F102 products.))

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

(T_A = −40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	
Transfer rate Note4		Reception	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V		f_{MCK}/6 Note1		f_{MCK}/6 Note1	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ Note3		4.0		1.3	Mbps
			2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V		f_{MCK}/6 Note1		f_{MCK}/6 Note1	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ Note3		4.0		1.3	Mbps
			1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		f_{MCK}/6 Notes1, 2		f_{MCK}/6 Notes1, 2	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ Note3		4.0		1.3	Mbps
		Transmission	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V		**Note4**		**Note4**	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 1.4 kΩ, V_b = 2.7 V		2.8 Note5		2.8 Note5	Mbps
			2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V,		**Note6**		**Note6**	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 2.7 kΩ, V_b = 2.3 V		1.2 Note7		1.2 Note7	Mbps
			1.8 V ≤ V_{DD} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		**Notes 2, 8**		**Notes 2, 8**	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 5.5 kΩ, V_b = 1.6 V		0.43 Note9		0.43 Note9	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. Use it with $V_{DD} \geq V_b$.

3. The maximum operating frequencies of the CPU/peripheral hardware clock (f_{CLK}) are:

HS (high-speed main) mode: 24 MHz (2.7 V ≤ V_{DD} ≤ 5.5 V)

16 MHz (2.4 V ≤ V_{DD} ≤ 5.5 V)

LS (low-speed main) mode: 8 MHz (1.8 V ≤ V_{DD} ≤ 5.5 V)

4. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V ≤ V_{DD} ≤ 5.5 V and 2.7 V ≤ V_b ≤ 4.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides.

(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCK00... internal clock output, corresponding CSI00 only)

(T_A = –40 to +85°C, 2.7 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		LS (low-speed main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	
SCK00 cycle time	t_{KCY1}	$t_{KCY1} \geq 2/f_{CLK}$	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ	200		1150		ns
			2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ	300		1150		ns
SCK00 high-level width	t_{KH1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		t_{KCY1}/2 – 50		t_{KCY1}/2– 50		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		t_{KCY1}/2 – 120		t_{KCY1}/2 – 120		ns
SCK00 low-level width	t_{KL1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		t_{KCY1}/2 – 7		t_{KCY1}/2 – 50		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		t_{KCY1}/2 – 10		t_{KCY1}/2 – 50		ns
SI00 setup time (to SCK00↑) Note 1	t_{SIK1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		58		479		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		121		479		ns
SI00 hold time (from SCK00↑) Note 1	t_{KSI1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		10		10		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		10		10		ns
Delay time from SCK00↓ to SO00 output Note 1	t_{KSO1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ			60		60	ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ			130		130	ns
SI00 setup time (to SCK00↓) Note 2	t_{SIK1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		23		110		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		33		110		ns
SI00 hold time (from SCK00↓) Note 2	t_{KSI1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		10		10		ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		10		10		ns
Delay time from SCK00↑ to SO00 output Note 2	t_{KSO1}	4.0 V ≤ V_{DD} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ			10		10	ns
		2.7 V ≤ V_{DD} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ			10		10	ns

(**Notes**, **Caution**, and **Remarks** are listed on the next page.)

Notes 1. When DAP00 = 0 and CKP00 = 0, or DAP00 = 1 and CKP00 = 1

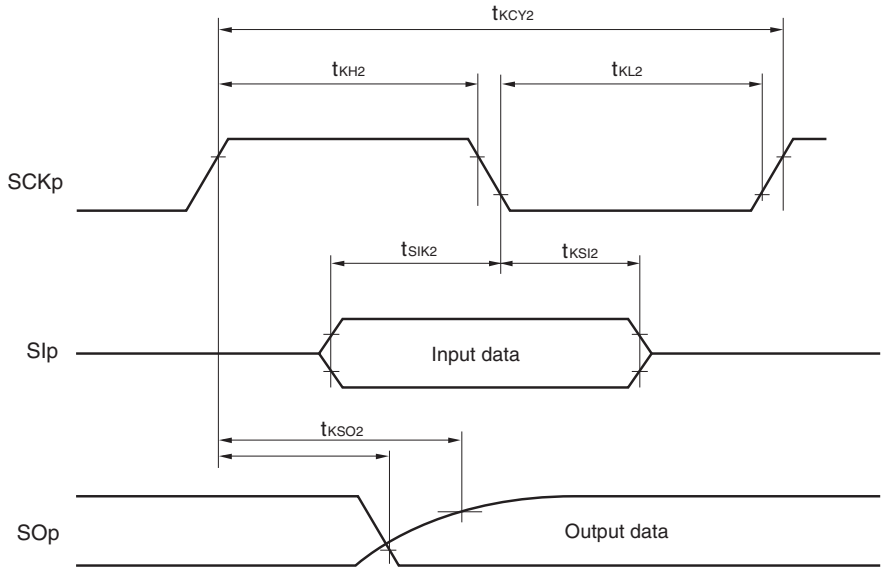
2. When DAP00 = 0 and CKP00 = 1, or DAP00 = 1 and CKP00 = 0.

Caution Select the TTL input buffer for the SI00 pin and the N-ch open drain output (V_{DD} tolerance) mode for the SO00 pin and SCK00 pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). **For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.**

Remarks 1. R_b [Ω]:Communication line (SCK00, SO00) pull-up resistance, C_b [F]: Communication line (SCK00, SO00) load capacitance, V_b [V]: Communication line voltage

2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register 0 (SPS0) and the CKS00 bit of serial mode register 00 (SMR00).)

CSI mode serial transfer timing (slave mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark p: CSI number (p = 00, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0)

2.5.2 Serial interface IICA

(T_A = −40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) mode / LS (low-speed main) mode				Unit
			Standard Mode		Fast Mode		
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	f_{SCL}	Fast mode: f_{CLK} ≥ 3.5 MHz			0	400	kHz
		Normal mode: f_{CLK} ≥ 1 MHz	0	100			kHz
Setup time of restart condition	$t_{SU:STA}$		4.7		0.6		μs
Hold time[Note 1]	$t_{HD:STA}$		4.0		0.6		μs
Hold time when SCLA0 = "L"	t_{LOW}		4.7		1.3		μs
Hold time when SCLA0 = "H"	t_{HIGH}		4.0		0.6		μs
Data setup time (reception)	$t_{SU:DAT}$		250		100		ns
Data hold time (transmission)[Note 2]	$t_{HD:DAT}$		0	3.45	0	0.9	μs
Setup time of stop condition	$t_{SU:STO}$		4.0		0.6		μs
Bus-free time	t_{BUF}		4.7		1.3		μs

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

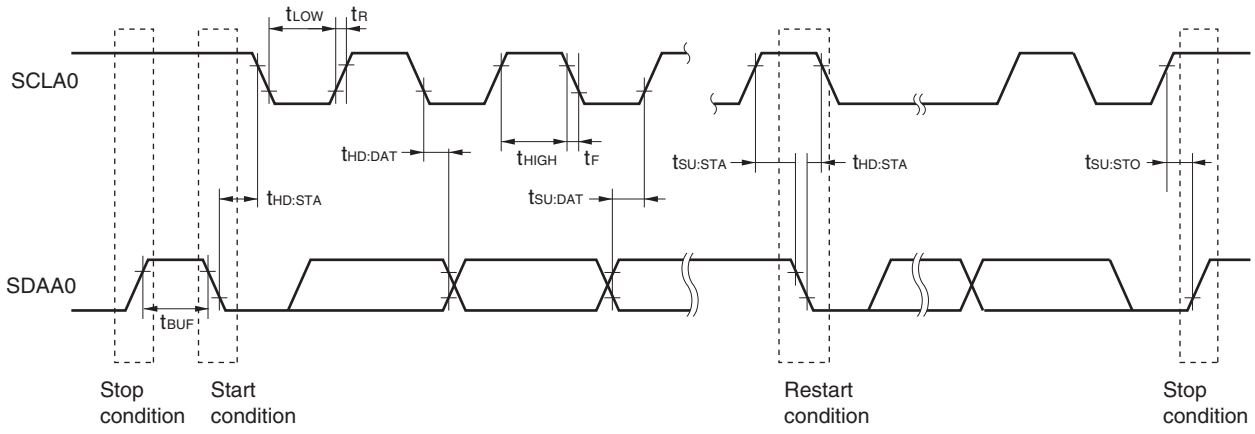
<R> **2.** The maximum value (MAX.) of $t_{HD:DAT}$ is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution Only in the 30-pin products, the values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (I_{OH1}, I_{OL1}, V_{OH1}, V_{OL1}) must satisfy the values in the redirect destination.

Remark The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

Normal mode: C_b = 400 pF, Rb = 2.7 kΩ
Fast mode: C_b = 320 pF, Rb = 1.1 kΩ

IICA serial transfer timing



2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel	Reference Voltage		
	Reference voltage (+) = AV_{REFP} Reference voltage (–) = AV_{REFM}	Reference voltage (+) = V_{DD} Reference voltage (–) = V_{SS}	Reference voltage (+) = V_{BGR} Reference voltage (–) = AV_{REFM}
ANI0 to ANI3	Refer to **28.6.1 (1)**.	Refer to **28.6.1 (3)**.	Refer to **28.6.1 (4)**.
ANI16 to ANI22	Refer to **28.6.1 (2)**.		
Internal reference voltage Temperature sensor output voltage	Refer to **28.6.1 (1)**.		–

(1) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (–) = AV_{REFM}/ANI1 (ADREFM = 1), target pin: ANI2, ANI3, internal reference voltage, and temperature sensor output voltage

(T_A = –40 to +85°C, 1.8 V ≤ AV_{REFP} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (–) = AV_{REFM} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error[Note 1]	AINL	10-bit resolution AV_{REFP} = V_{DD} [Note 3]			1.2	±3.5	LSB
					1.2	±7.0 [Note 4]	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI2, ANI3	3.6 V ≤ V_{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.1875		39	μs
			1.8 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
				57		95	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V_{DD} ≤ 5.5 V	2.375		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.5625		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Zero-scale error[Notes 1, 2]	EZS	10-bit resolution AV_{REFP} = V_{DD} [Note 3]				±0.25	%FSR
						±0.50 [Note 4]	%FSR
Full-scale error[Notes 1, 2]	EFS	10-bit resolution AV_{REFP} = V_{DD} [Note 3]				±0.25	%FSR
						±0.50 [Note 4]	%FSR
Integral linearity error[Note 1]	ILE	10-bit resolution AV_{REFP} = V_{DD} [Note 3]				±2.5	LSB
						±5.0 [Note 4]	LSB
Differential linearity error [Note 1]	DLE	10-bit resolution AV_{REFP} = V_{DD} [Note 3]				±1.5	LSB
						±2.0 [Note 4]	LSB
Analog input voltage	V_{AIN}	ANI2, ANI3		0		AV_{REFP}	V
		Internal reference voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)		V_{BGR} [Note 5]			V
		Temperature sensor output voltage (2.4 V ≤ V_{DD} ≤ 5.5 V, HS (high-speed main) mode)		V_{TMPS25} [Note 5]			V

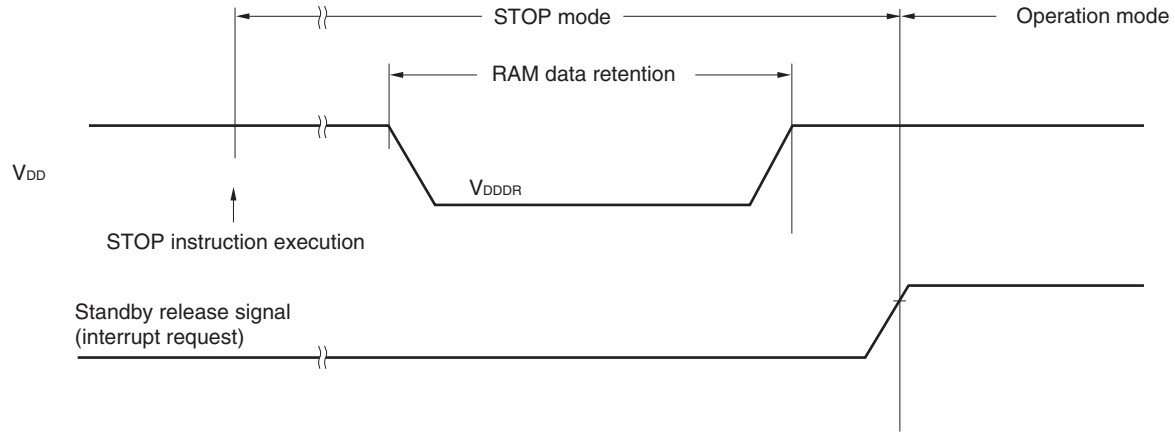
(**Notes** are listed on the next page.)

<R> 2.7 Data Memory STOP Mode Low Supply Voltage Data Retention Characteristics

(T_A = −40 to +85°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{DDDR}		1.46 Note		5.5	V

<R> **Note** This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



2.8 Flash Memory Programming Characteristics

(T_A = −40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

<R>

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	f_{CLK}		1		24	MHz
Code flash memory rewritable times Notes 1, 2, 3	C_{erwr}	Retained for 20 years T_A = 85°C	1,000			Times
Data flash memory rewritable times Notes 1, 2, 3		Retained for 1 year T_A = 25°C		1,000,000		
		Retained for 5 years T_A = 85°C	100,000			
		Retained for 20 years T_A = 85°C	10,000			

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

2. When using flash memory programmer and Renesas Electronics self programming library

3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

<R> 3. ELECTRICAL SPECIFICATIONS (G: INDUSTRIAL APPLICATIONS T_A = –40 to +105°C)

<R> This chapter describes the following electrical specifications.

Target products G: Industrial applications T_A = -40 to +105°C

<R> R5F102xxGxx

Cautions 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.

2. The pins mounted depend on the product. Refer to 2.1 Port Functions to 2.2.1 Functions for each product.

3. Please contact Renesas Electronics sales office for derating of operation under T_A = +85°C to +105°C. Derating is the systematic reduction of load for the sake of improved reliability.

Remark When the RL78 microcontroller is used in the range of T_A = -40 to +85 °C, see CHAPTER 28

<R> **ELECTRICAL SPECIFICATIONS (A: T_A = -40 to +85 °C).**

There are following differences between the products "G: Industrial applications (T_A = -40 to +105°C)" and the products “A: Consumer applications, and D: Industrial applications”.

Parameter	Application	
	A: Consumer applications, D: Industrial applications	G: Industrial applications
Operating ambient temperature	T_A = -40 to +85°C	T_A = -40 to +105°C
Operating mode Operating voltage range	HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 24 MHz 2.4 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 16 MHz LS (low-speed main) mode: 1.8 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 8 MHz	HS (high-speed main) mode only: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 24 MHz 2.4 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 16 MHz
High-speed on-chip oscillator clock accuracy	R5F102 products, 1.8 V ≤ V_{DD} ≤ 5.5 V: ±1.0%@ T_A = -20 to +85°C ±1.5%@ T_A = -40 to -20°C R5F103 products, 1.8 V ≤ V_{DD} ≤ 5.5 V: ±5.0%@ T_A = -40 to +85°C	R5F102 products, 2.4 V ≤ V_{DD} ≤ 5.5 V: ±2.0%@ T_A = +85 to +105°C ±1.0%@ T_A = -20 to +85°C ±1.5%@ T_A = -40 to -20°C
Serial array unit	UART CSI: f_{CLK}/2 (supporting 12 Mbps), f_{CLK}/4 Simplified I^2C communication	UART CSI: f_{CLK}/4 Simplified I^2C communication
Voltage detector	Rise detection voltage: 1.88 V to 4.06 V (12 levels) Fall detection voltage: 1.84 V to 3.98 V (12 levels)	Rise detection voltage: 2.61 V to 4.06 V (8 levels) Fall detection voltage: 2.55 V to 3.98 V (8 levels)

Remark The electrical characteristics of the products G: Industrial applications (T_A = -40 to +105°C) are different from those of the products “A: Consumer applications, and D: Industrial applications”. For details, refer to **29.1** to **29.10**.

3.1 Absolute Maximum Ratings

Absolute Maximum Ratings (T_A = 25°C)

Parameter	Symbols	Conditions		Ratings	Unit
Supply Voltage	V_{DD}			−0.5 to + 6.5	V
REGC terminal input voltage[Note1]	V_{IREGC}	REGC		−0.3 to +2.8 and −0.3 to V_{DD} + 0.3 [Note 2]	V
Input Voltage	V_{I1}	Other than P60, P61		−0.3 to V_{DD} + 0.3[Note 3]	V
	V_{I2}	P60, P61 (N-ch open drain)		−0.3 to 6.5	V
Output Voltage	V_O			−0.3 to V_{DD} + 0.3[Note 3]	V
Analog input voltage	V_{AI}	20, 24-pin products: ANI0 to ANI3, ANI16 to ANI22 30-pin products: ANI0 to ANI3, ANI16 to ANI19		−0.3 to V_{DD} + 0.3 and −0.3 to AVREF(+)+0.3 [Notes 3, 4]	V
Output current, high	I_{OH1}	Per pin	Other than P20 to P23	−40	mA
		Total of all pins	All the terminals other than P20 to P23	−170	mA
			20-, 24-pin products: P40 to P42 30-pin products: P00, P01, P40, P120	−70	mA
			20-, 24-pin products: P00 to P03[Note 5], P10 to P14 30-pin products: P10 to P17, P30, P31, P50, P51, P147	−100	mA
	I_{OH2}	Per pin	P20 to P23	−0.5	mA
		Total of all pins		−2	mA
Output current, low	I_{OL1}	Per pin	Other than P20 to P23	40	mA
		Total of all pins	All the terminals other than P20 to P23	170	mA
			20-, 24-pin products: P40 to P42 30-pin products: P00, P01, P40, P120	70	mA
			20-, 24-pin products: P00 to P03 [Note 5], P10 to P14, P60, P61 30-pin products: P10 to P17, P30, P31, P50, P51, P60, P61, P147	100	mA
	I_{OL2}	Per pin	P20 to P23	1	mA
		Total of all pins		5	mA
Operating ambient temperature	T_A			−40 to +105	°C
Storage temperature	T_{stg}			−65 to +150	°C

Notes 1. 30-pin product only.

2. Connect the REGC pin to V_{SS} via a capacitor (0.47 to 1 μF). This value determines the absolute maximum rating of the REGC pin. Do not use it with voltage applied.

3. Must be 6.5 V or lower.

4. Do not exceed $AV_{REF}(+)$ + 0.3 V in case of A/D conversion target pin.

5. 24-pin products only.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remarks 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2. $AV_{REF}(+)$: + side reference voltage of the A/D converter.

3. V_{SS} : Reference voltage

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) (2/4)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low[Note 1]	I_{OL1}	20-, 24-pin products: Per pin for P00 to P03[Note 4], P10 to P14, P40 to P42 30-pin products: Per pin for P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147				8.5 [Note 2]	mA
		Per pin for P60, P61				15.0 [Note 2]	mA
		20-, 24-pin products: Total of P40 to P42 30-pin products: Total of P00, P01, P40, P120 (When duty ≤ 70% [Note 3])	4.0 V ≤ V_{DD} ≤ 5.5 V			25.5	mA
			2.7 V ≤ V_{DD} < 4.0 V			9.0	mA
			2.4 V ≤ V_{DD} < 2.7 V			1.8	mA
		20-, 24-pin products: Total of P00 to P03[Note 4], P10 to P14, P60, P61 30-pin products: Total of P10 to P17, P30, P31, P50, P51, P60, P61, P147 (When duty ≤ 70% [Note 3])	4.0 V ≤ V_{DD} ≤ 5.5 V			40.0	mA
			2.7 V ≤ V_{DD} < 4.0 V			27.0	mA
			2.4 V ≤ V_{DD} < 2.7 V			5.4	mA
		Total of all pins (When duty ≤ 70% [Note 3])				65.5	mA
	I_{OL2}	Per pin for P20 to P23				0.4	mA
		Total of all pins				1.6	mA

Notes 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the V_{SS} pin.

2. However, do not exceed the total current value.

3. The output current value under conditions where the duty factor ≤ 70%.
If duty factor > 70%: The output current value can be calculated with the following expression (where n represents the duty factor as a percentage).

- Total output current of pins = (I_{OL} × 0.7)/(n × 0.01)

<Example> Where n = 80% and I_{OL} = 10.0 mA

Total output current of pins = (10.0 × 0.7)/(80 × 0.01) ≅ 8.7 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

4. 24-pin products only.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(1) 20-, 24-pin products

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V) **(2/2)**

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit
Supply current[Note 1]	I_{DD2}[Note 2]	HALT mode	HS (High-speed main) mode[Note 6]	f_{IH} = 24 MHz[Note 4]	V_{DD} = 5.0 V		440	2230	μA
					V_{DD} = 3.0 V		440	2230	
				f_{IH} = 16 MHz[Note 4]	V_{DD} = 5.0 V		400	1650	μA
					V_{DD} = 3.0 V		400	1650	
				f_{MX} = 20 MHz[Note 3], V_{DD} = 5.0 V	Square wave input		280	1900	μA
					Resonator connection		450	2000	
				f_{MX} = 20 MHz[Note 3], V_{DD} = 3.0 V	Square wave input		280	1900	μA
					Resonator connection		450	2000	
				f_{MX} = 10 MHz[Note 3], V_{DD} = 5.0 V	Square wave input		190	1010	μA
					Resonator connection		260	1090	
				f_{MX} = 10 MHz[Note 3], V_{DD} = 3.0 V	Square wave input		190	1010	μA
					Resonator connection		260	1090	
	I_{DD3}[Note 5]	STOP mode	T_A = –40°C				0.19	0.50	μA
			T_A = +25°C				0.24	0.50	
			T_A = +50°C				0.32	0.80	
			T_A = +70°C				0.48	1.20	
			T_A = +85°C				0.74	2.20	
			T_A = +105°C				1.50	10.20	

Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

2. During HALT instruction execution by flash memory.

3. When high-speed on-chip oscillator clock is stopped.

4. When high-speed system clock is stopped.

5. Not including the current flowing into the 12-bit interval timer and watchdog timer.

6. Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS (High speed main) mode: V_{DD} = 2.7 V to 5.5 V @1 MHz to 24 MHz

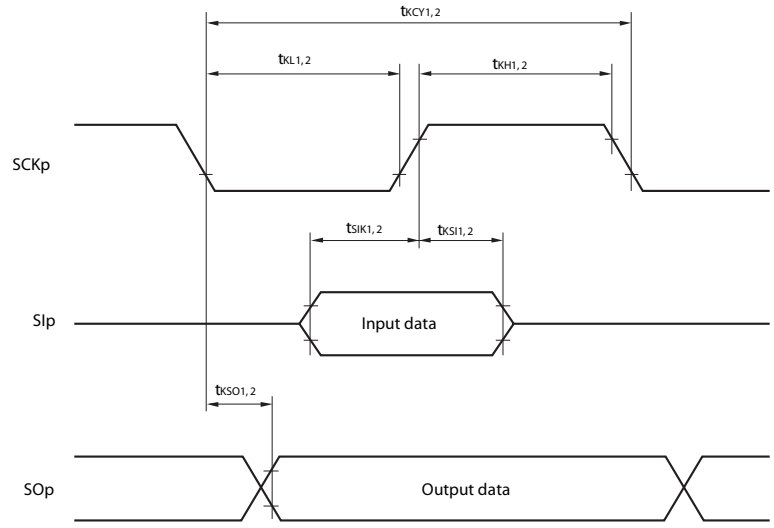
V_{DD} = 2.4 V to 5.5 V @1 MHz to 16 MHz

Remarks 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

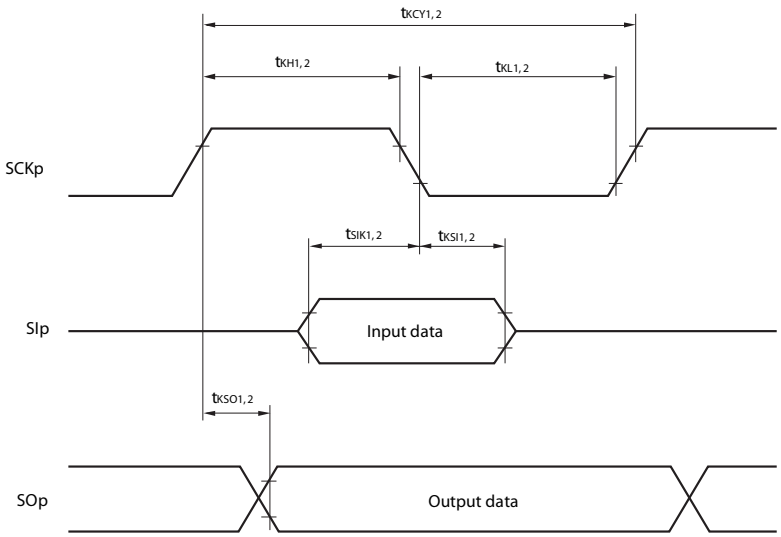
2. f_{IH}: high-speed on-chip oscillator clock frequency

3. Except temperature condition of the TYP. value is T_A = 25°C, other than STOP mode

CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01, 11, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0, 1, 3)

2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0,1), n: Channel number (n = 0, 1, 3))

3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel	Reference Voltage		
	Reference voltage (+) = AV_{REFP} Reference voltage (–) = AV_{REFM}	Reference voltage (+) = V_{DD} Reference voltage (–) = V_{SS}	Reference voltage (+) = V_{BGR} Reference voltage (–) = AV_{REFM}
ANI0 to ANI3	Refer to **29.6.1 (1)**.	Refer to **29.6.1 (3)**.	Refer to **29.6.1 (4)**.
ANI16 to ANI22	Refer to **29.6.1 (2)**.		
Internal reference voltage Temperature sensor output voltage	Refer to **29.6.1 (1)**.		–

(1) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (–) = AV_{REFM}/ANI1 (ADREFM = 1), target pin: ANI2, ANI3, internal reference voltage, and temperature sensor output voltage

(T_A = –40 to +105°C, 2.4 V ≤ AV_{REFP} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (–) = AV_{REFM} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error[Note 1]	AINL	10-bit resolution AV_{REFP} = V_{DD} [Note 3]			1.2	±3.5	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI2, ANI3	3.6 V ≤ V_{DD} ≤ 5.5 V	2.125		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.1875		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V_{DD} ≤ 5.5 V	2.375		39	μs
			2.7 V ≤ V_{DD} ≤ 5.5 V	3.5625		39	μs
			2.4 V ≤ V_{DD} ≤ 5.5 V	17		39	μs
Zero-scale error[Notes 1, 2]	EZS	10-bit resolution AV_{REFP} = V_{DD} [Note 3]				±0.25	%FSR
Full-scale error[Notes 1, 2]	EFS	10-bit resolution AV_{REFP} = V_{DD} [Note 3]				±0.25	%FSR
Integral linearity error[Note 1]	ILE	10-bit resolution AV_{REFP} = V_{DD} [Note 3]				±2.5	LSB
Differential linearity error [Note 1]	DLE	10-bit resolution AV_{REFP} = V_{DD} [Note 3]				±1.5	LSB
Analog input voltage	V_{AIN}	ANI2, ANI3		0		AV_{REFP}	V
		Internal reference voltage (HS (high-speed main) mode)		V_{BGR} [Note 4]			V
		Temperature sensor output voltage (HS (high-speed main) mode)		V_{TMPS25} [Note 4]			V

(**Notes** are listed on the next page.)

LVD detection voltage of interrupt & reset mode

(T_A = –40 to +105°C, $V_{PDR} \leq V_{DD} \leq$ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Interrupt and reset mode	V_{LVDD0}	V_{POC2}, V_{POC1}, V_{POC1} = 0, 1, 1, falling reset voltage			2.64	2.75	2.86	V
	V_{LVDD1}		LVIS1, LVIS0 = 1, 0	Rising reset release voltage	2.81	2.92	3.03	V
				Falling interrupt voltage	2.75	2.86	2.97	V
	V_{LVDD2}		LVIS1, LVIS0 = 0, 1	Rising reset release voltage	2.90	3.02	3.14	V
				Falling interrupt voltage	2.85	2.96	3.07	V
	V_{LVDD3}		LVIS1, LVIS0 = 0, 0	Rising reset release voltage	3.90	4.06	4.22	V
				Falling interrupt voltage	3.83	3.98	4.13	V

3.6.5 Power supply voltage rising slope characteristics

(T_A = –40 to +105°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	S_{VDD}				54	V/ms

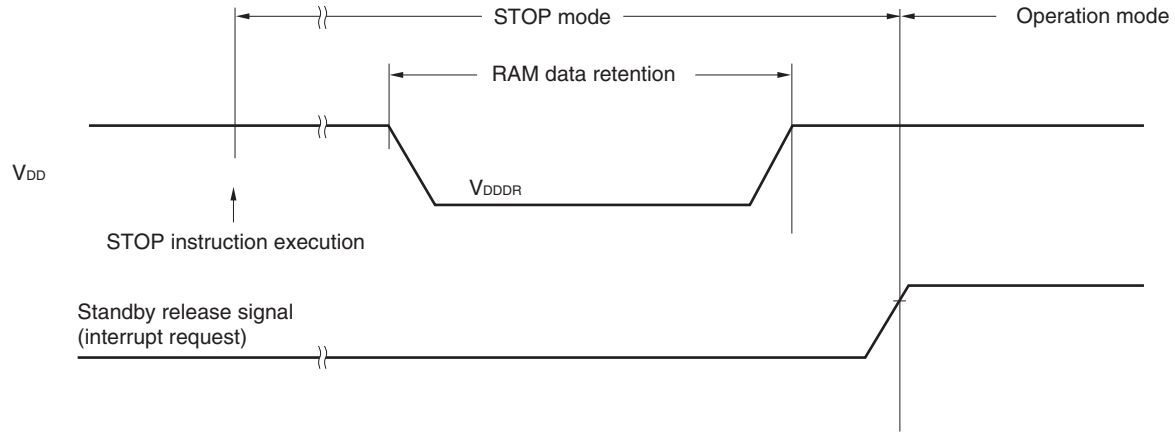
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 29.4 AC Characteristics.

<R> 3.7 RAM Data Retention Characteristics

(T_A = –40 to +105°C, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{DDDR}		1.44 Note		5.5	V

<R> Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



3.8 Flash Memory Programming Characteristics

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
<R> System clock frequency	f_{CLK}		1		24	MHz
Code flash memory rewritable times Notes 1, 2, 3	C_{erwr}	Retained for 20 years T_A = 85°C Notes 4	1,000			Times
Data flash memory rewritable times Notes 1, 2, 3		Retained for 1 year T_A = 25°C Notes 4		1,000,000		
		Retained for 5 years T_A = 85°C Notes 4	100,000			
		Retained for 20 years T_A = 85°C Notes 4	10,000			

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

2. When using flash memory programmer and Renesas Electronics self programming library

3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

4. This temperature is the average value at which data are retained.

3.9 Dedicated Flash Memory Programmer Communication (UART)

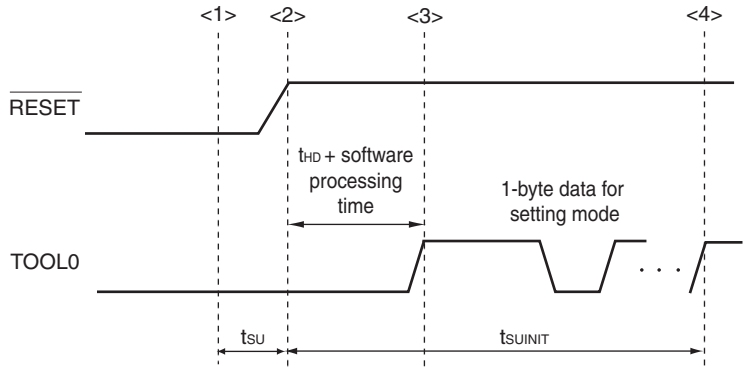
(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

3.10 Timing of Entry to Flash Memory Programming Modes

(T_A = –40 to +105°C, 2.4 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	t_{SUINIT}	POR and LVD reset are released before external release			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	t_{SU}	POR and LVD reset are released before external release	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	t_{HD}	POR and LVD reset are released before external release	1			ms



<1> The low level is input to the TOOL0 pin.
<2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
<3> The TOOL0 pin is set to the high level.
<4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark t_{SUINIT}: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.
t_{SU}: Time to release the external reset after the TOOL0 pin is set to the low level
t_{HD}: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)